

Application Specific Discretes  
A.S.D.™

## PROGRAMMABLE TRANSIENT VOLTAGE SUPPRESSOR FOR SLIC PROTECTION

### FEATURES

- BIDIRECTIONAL FUNCTION WITH VOLTAGE PROGRAMMABILITY IN BOTH POSITIVE AND NEGATIVE POLARITIES.
- PROGRAMMABLE BREAKDOWN VOLTAGE UP TO 100 V.
- HOLDING CURRENT = 150 mA min.
- HIGH SURGE CURRENT CAPABILITY.  
 $I_{PP} = 100A, 10/1000\mu s$

### DESCRIPTION

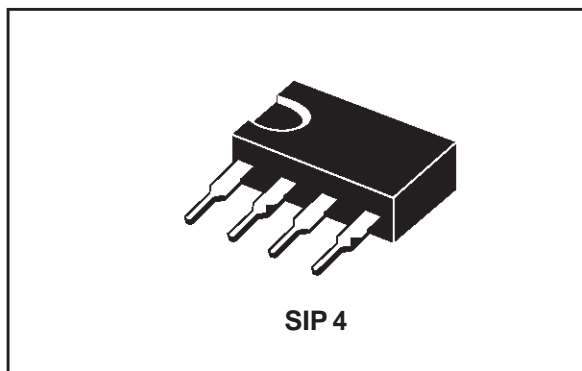
This device has been especially designed to protect a subscriber line interface circuit (SLIC) with an integrated ring generator.

Used with the recommended application circuit, each line (TIP and RING) is protected against positive and negative surges. In the positive polarity, the breakdown voltage is referenced to the + VB, and in the negative polarity, the breakdown voltage is referenced to the -Vbat.

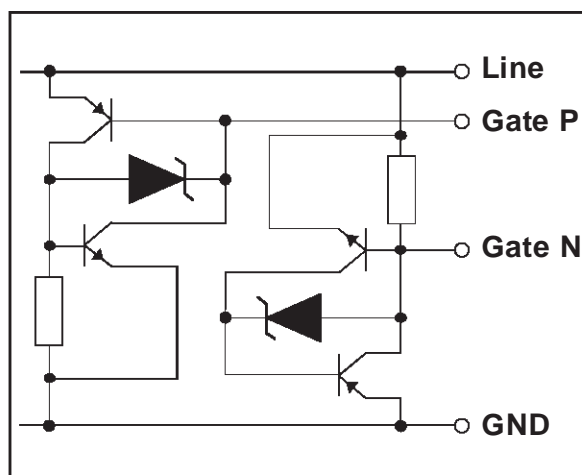
Its high surge current capability makes the L3121B a reliable protection device for very exposed equipment, or when series resistors are very low.

### IN ACCORDANCE WITH FOLLOWING STANDARDS

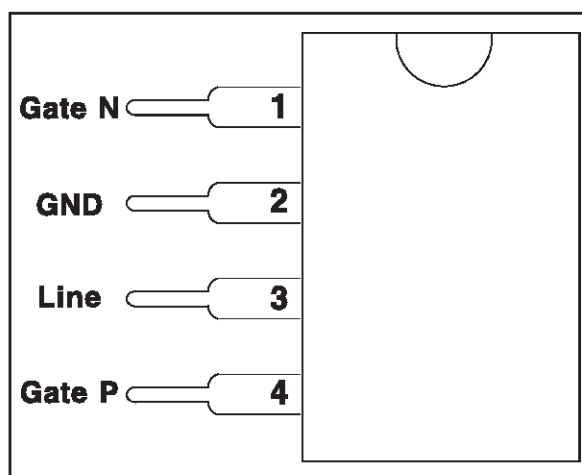
<b>CCITT K20</b>	10/700 $\mu s$	1 kV
	5/310 $\mu s$	25 A
<b>VDE 0433</b>	10/700 $\mu s$	2 kV
	5/310 $\mu s$	50 A
<b>CNET</b>	0.5/700 $\mu s$	1 kV
	0.2/310 $\mu s$	25 A



### SCHEMATIC DIAGRAM



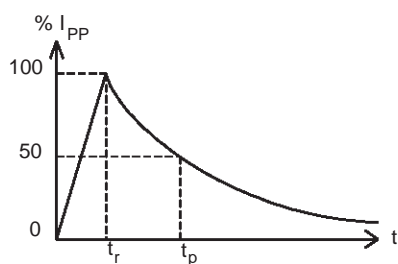
### CONNECTION DIAGRAM



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**L3121B****ABSOLUTE MAXIMUM RATINGS** ( $T_{amb} = 25^{\circ}\text{C}$ )

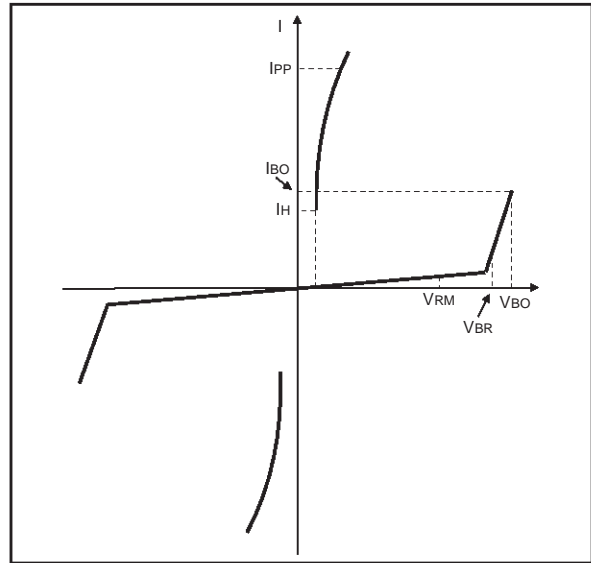
Symbol	Parameter		Value	Unit
$I_{PP}$	Peak pulse current	10/1000 $\mu\text{s}$ 8/20 $\mu\text{s}$	100 250	A
$I_{TSM}$	Non repetitive surge peak on-state current	$t_p = 10 \text{ ms}$	50	A
$V_{MLG}$ $V_{MGL}$	Maximum voltage LINE/GND. Maximum voltage GATE/LINE.		100 80	V V
$T_{stg}$ $T_j$	Storage temperature range Maximum operating junction temperature		- 40 to + 150 + 150	$^{\circ}\text{C}$ $^{\circ}\text{C}$
$T_L$	Maximum lead temperature for soldering during 10s		260	$^{\circ}\text{C}$

Pulse waveform 10/1000 $\mu\text{s}$ **THERMAL RESISTANCE**

Symbol	Parameter	Value	Unit
$R_{th(j-a)}$	Junction-to-ambient	80	$^{\circ}\text{C/W}$

**ELECTRICAL CHARACTERISTICS** ( $T_{amb} = 25\text{ }^{\circ}\text{C}$ )

Symbol	Parameter
$V_{RM}$	Stand-off voltage
$I_{RM}$	Reverse leakage current
$V_{BR}$	Breakdown voltage
$V_{BO}$	Breakover voltage
$I_H$	Holding current
$I_{BO}$	Breakover current
$I_{PP}$	Peak pulse current
$V_{GN}$	Gate voltage
$I_{GN}, I_{GP}$	Triggering gate current
C	Capacitance

**1- OPERATION WITHOUT GATE**

Type	$I_{RM} @ V_{RM}$ max.		$V_{BR} @ I_R$ min.		$V_{BO} @ I_{BO}$ max. typ. max. note 1			$I_H$ min. note 1	C max. note 2
	$\mu\text{A}$	V	V	mA	V	mA	mA	mA	pF
	L3121B	5 8	60 90	100	1	180	200	500	150 200

**2- OPERATION WITH GATE**

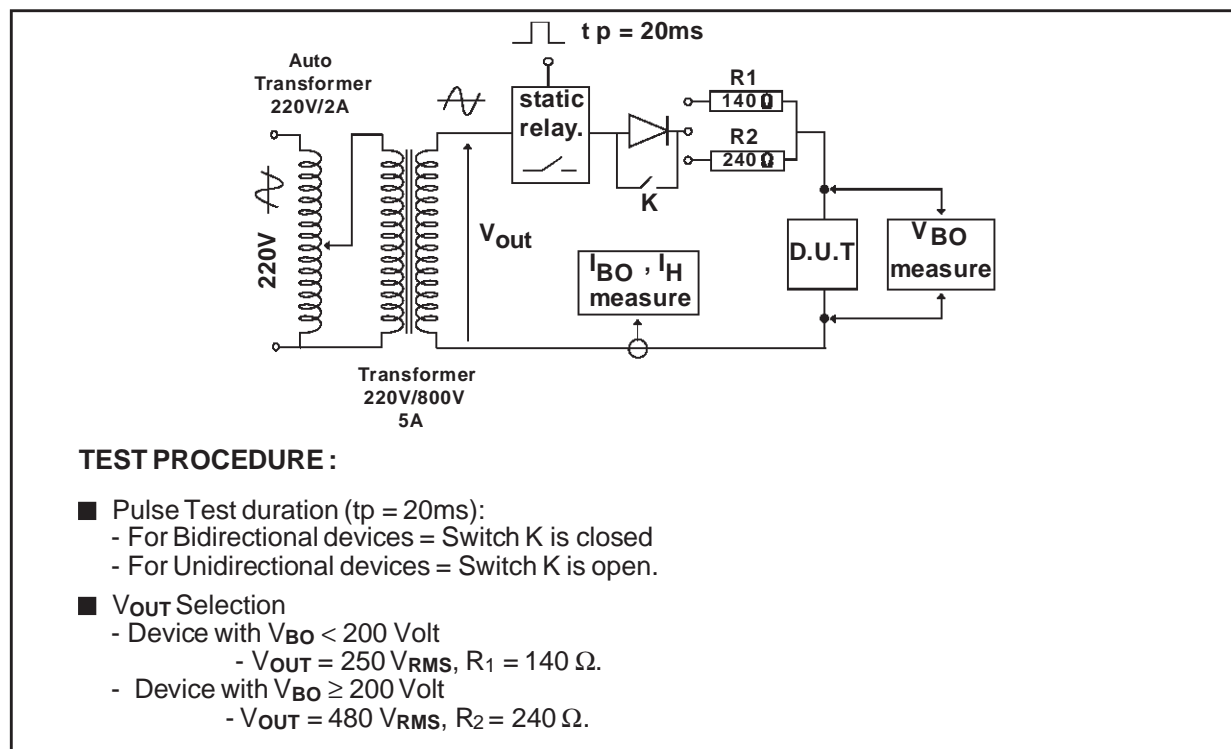
Type	V <sub>GN</sub> @ I <sub>GN</sub> = 200mA		I <sub>GN</sub> @ V <sub>AC</sub> = 60V		I <sub>GP</sub> @ V <sub>AC</sub> = 60V
	min.	max.	min.	max.	max.
	V	V	mA	mA	mA
L3121B	0.6	1.8	80	200	180

**Note 1 :** See the reference test circuits for  $I_H$ ,  $I_{BO}$  and  $V_{BO}$  parameters.

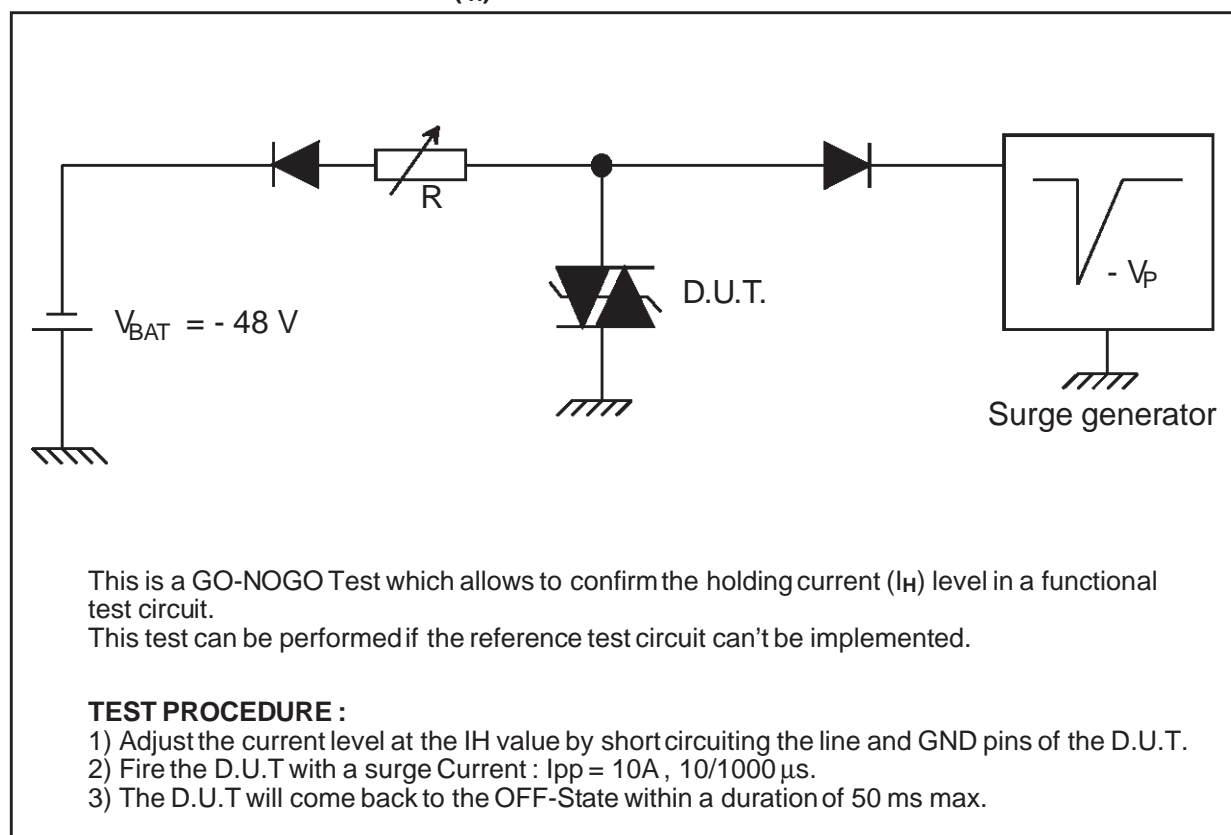
**Note 2 :**  $V_R = 5\text{ V}$ ,  $F = 1\text{ MHz}$ .

## L3121B

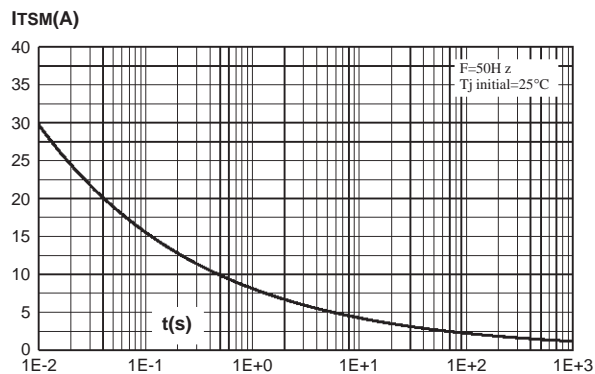
### REFERENCE TEST CIRCUIT FOR $I_{BO}$ and $V_{BO}$ parameters:



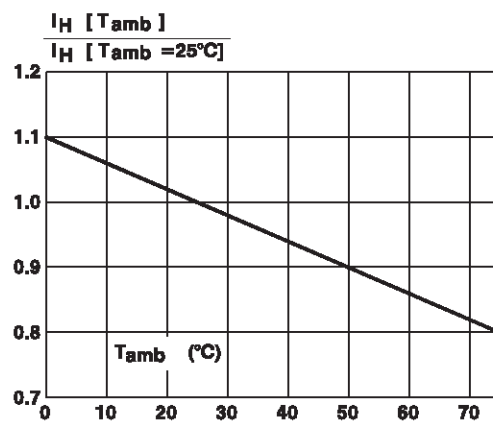
### FUNCTIONAL HOLDING CURRENT ( $I_H$ ) TEST CIRCUIT = GO - NOGO TEST.



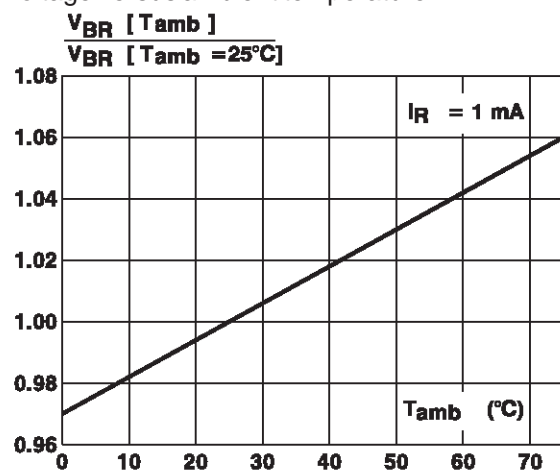
**Figure 1** : Surge peak current versus overload duration (typical values).



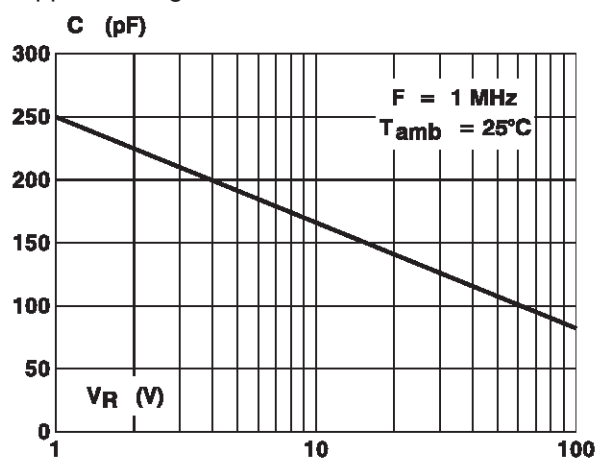
**Figure 2** : Relative variation of holding current versus junction temperature.



**Figure 3** : Relative variation of breakdown voltage versus ambient temperature.



**Figure 4** : Junction capacitance versus reverse applied voltage.

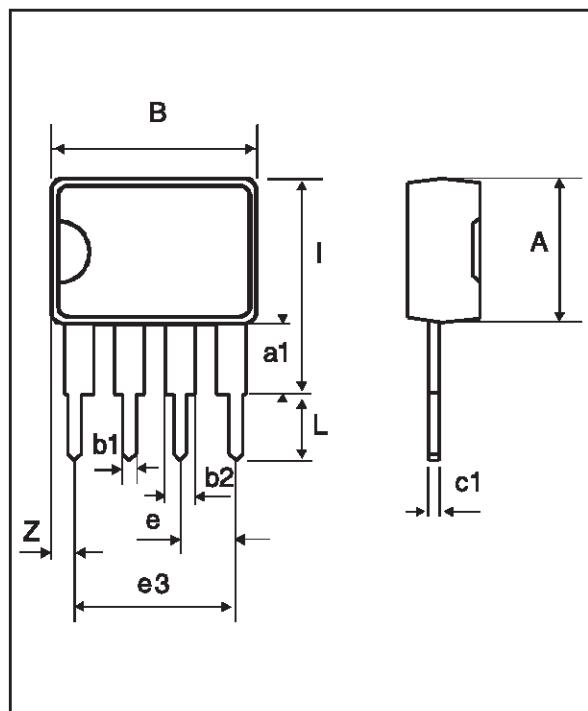


### Typical Slic Protection Concept.



**PACKAGE MECHANICAL DATA**

SIP 4 (Plastic)



REF.	DIMENSIONS					
	Millimetres			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A			7.10			0.280
a1	2.80			0.110		
B			10.15			0.400
b1		0.50			0.020	
b2	1.35		1.75	0.053		0.069
c1	0.38		0.50	0.015		0.020
e		2.54			0.100	
e3		7.62			0.200	
I			10.50			0.413
L		3.30			0.130	
Z			1.50			0.059

**PACKAGING :** Products supplied in antistatic tubes**WEIGHT :** 0.55g

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